



PJD15P06A

60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-15 A

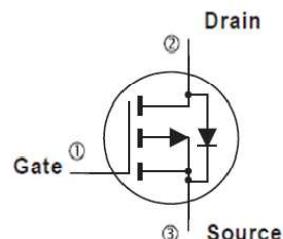
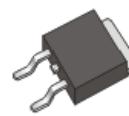
TO-252AA

Features

- $R_{DS(ON)}$, $V_{GS} @ -10V$, $I_D @ -7.5A < 68m\Omega$
- $R_{DS(ON)}$, $V_{GS} @ -4.5V$, $I_D @ -4.0A < 85m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0105 ounces, 0.297 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $T_c=25^\circ C$	I_D	-15	A
$T_c=100^\circ C$	I_D	-9.5	
Pulsed Drain Current ^(Note 1)	I_{DM}	-60	
Power Dissipation $T_c=25^\circ C$	P_D	25	W
$T_c=100^\circ C$	P_D	10	
Continuous Drain Current $T_A=25^\circ C$	I_D	-4.0	A
$T_A=70^\circ C$	I_D	-3.2	A
Power Dissipation	P_D	2.0	W
$T_A=70^\circ C$	P_D	1.3	
Single Pulse Avalanche Energy ^(Note 6)	E_{AS}	31	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	°C
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	5.0	°C/W
	Junction to Ambient	62.5	

- Limited only by Maximum Junction Temperature



PJD15P06A

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-60	-	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1.0	-1.63	-2.5	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-7.5\text{A}$	-	55	68	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4.0\text{A}$	-	73	85	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-60\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1.0	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Dynamic ^(Note 7)						
Total Gate Charge	Q_g	$V_{\text{DS}}=-30\text{V}, I_{\text{D}}=-7.5\text{A}, V_{\text{GS}}=-10\text{V}$ ^(Note 3)	-	17	-	nC
Gate-Source Charge	Q_{gs}		-	2.8	-	
Gate-Drain Charge	Q_{gd}		-	3.6	-	
Input Capacitance	C_{iss}	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}, f=1.0\text{MHz}$	-	879	-	pF
Output Capacitance	C_{oss}		-	70	-	
Reverse Transfer Capacitance	C_{rss}		-	47	-	
Turn-On Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=-30\text{V}, I_{\text{D}}=-1\text{A}, V_{\text{GS}}=-10\text{V}, R_{\text{G}}=6\Omega$ ^(Note 3)	-	8.4	-	ns
Turn-On Rise Time	t_r		-	30	-	
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	52	-	
Turn-Off Fall Time	t_f		-	16	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_s	---	-	-	-15	A
Diode Forward Voltage	V_{SD}	$I_s=-1\text{A}, V_{\text{GS}}=0\text{V}$	-	-0.73	-1.0	V

NOTES :

1. Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics
3. Repetitive rating, pulse width limited by junction temperature $T_J(\text{MAX})=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.
4. The maximum current rating is package limited
5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
6. $L=0.1\text{mH}, I_{\text{AS}}=-25\text{A}, V_{\text{GS}}=-10\text{V}, V_{\text{DS}}=-25\text{V}, R_{\text{G}}=25\text{ ohm}$
7. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

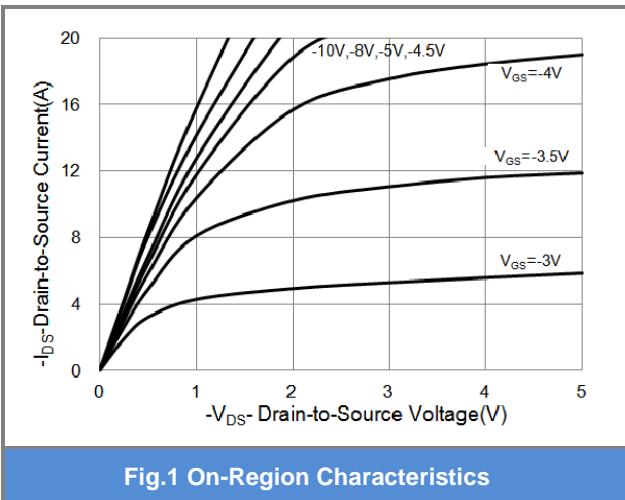


Fig.1 On-Region Characteristics

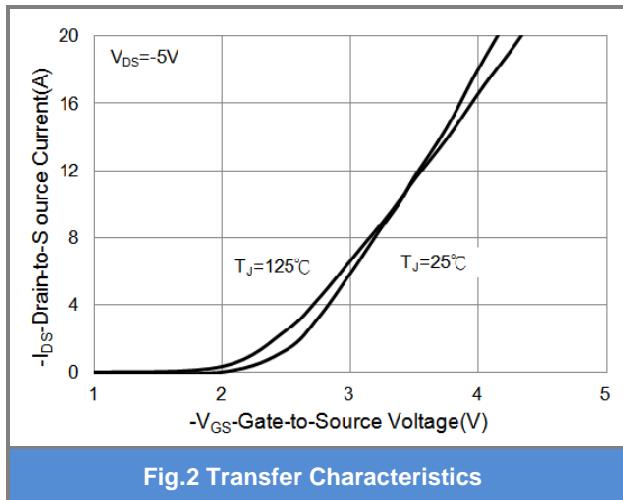


Fig.2 Transfer Characteristics

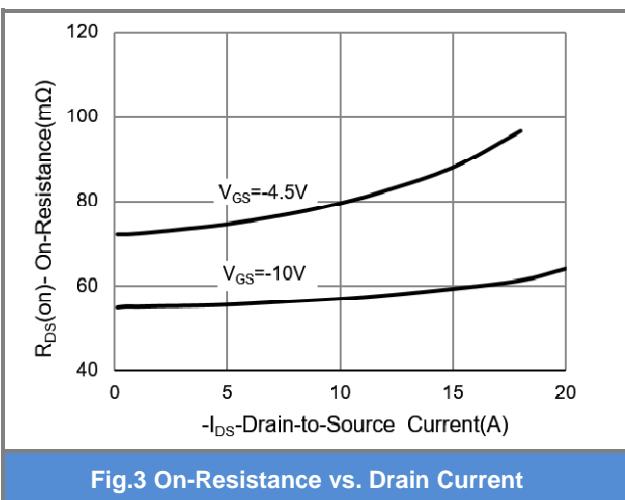


Fig.3 On-Resistance vs. Drain Current

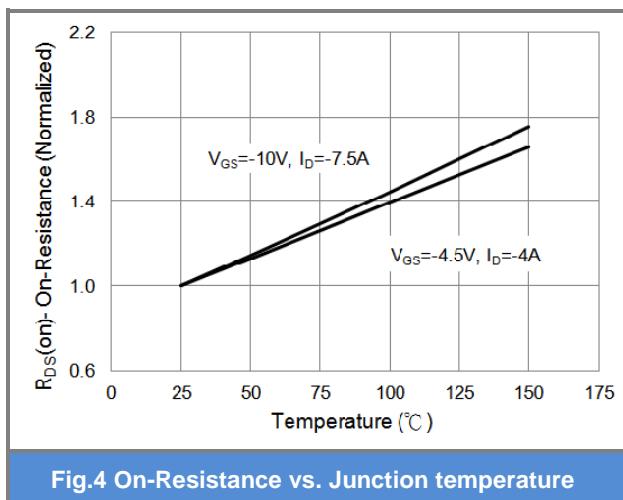


Fig.4 On-Resistance vs. Junction temperature

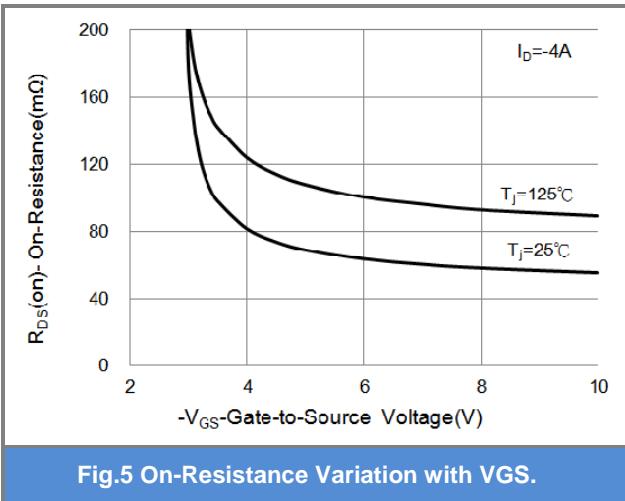


Fig.5 On-Resistance Variation with VGS.

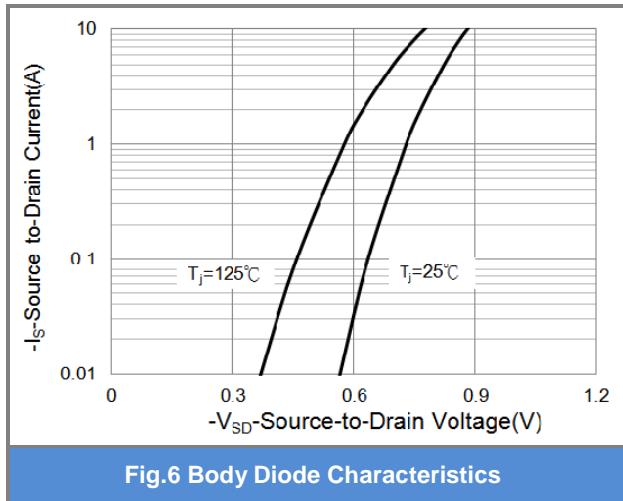


Fig.6 Body Diode Characteristics



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TYPICAL CHARACTERISTIC CURVES

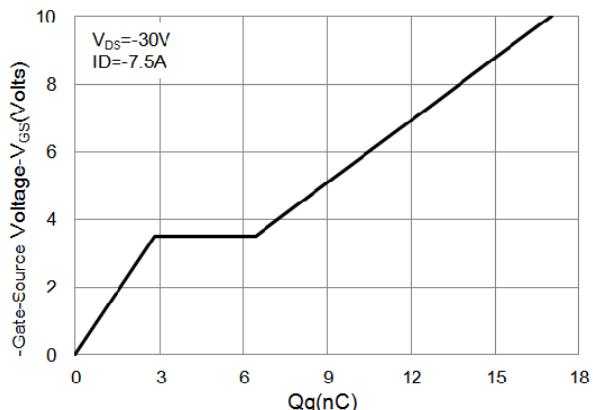


Fig.7 Gate-Charge Characteristics

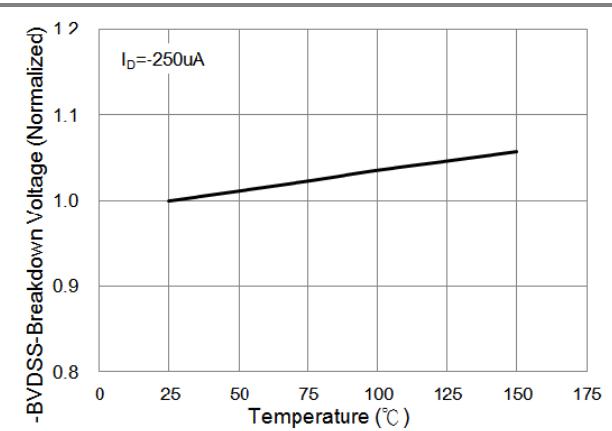


Fig.8 Breakdown Voltage Variation vs. Temperature

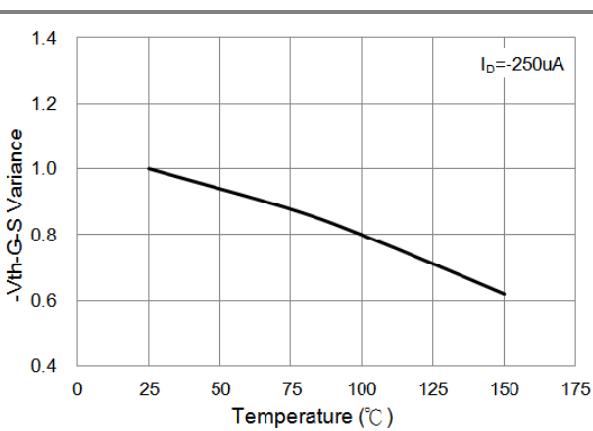


Fig.9 Threshold Voltage Variation with Temperature

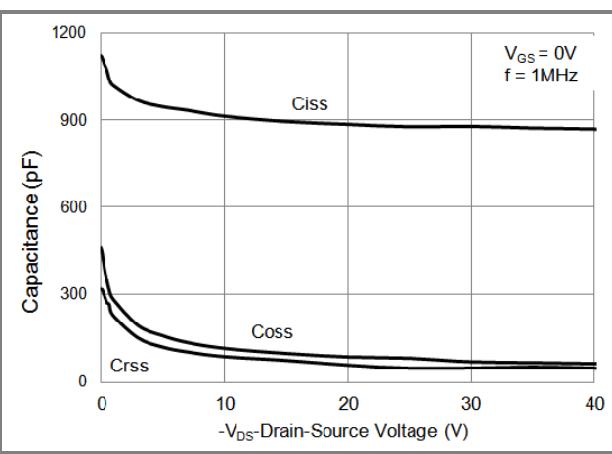


Fig.10 Capacitance vs. Drain-Source Voltage

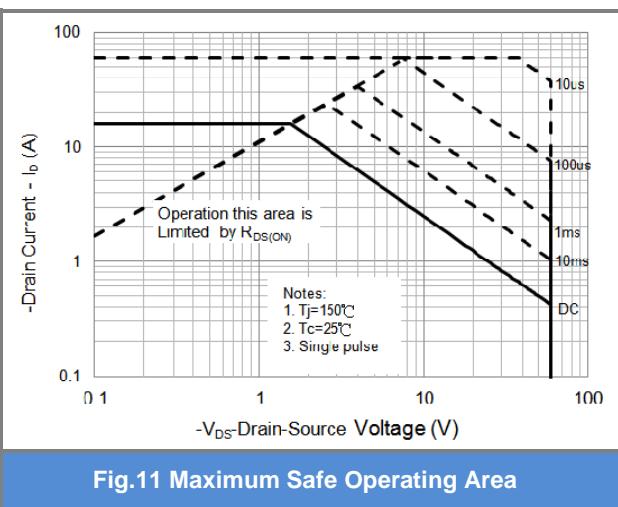


Fig.11 Maximum Safe Operating Area



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TYPICAL CHARACTERISTIC CURVES

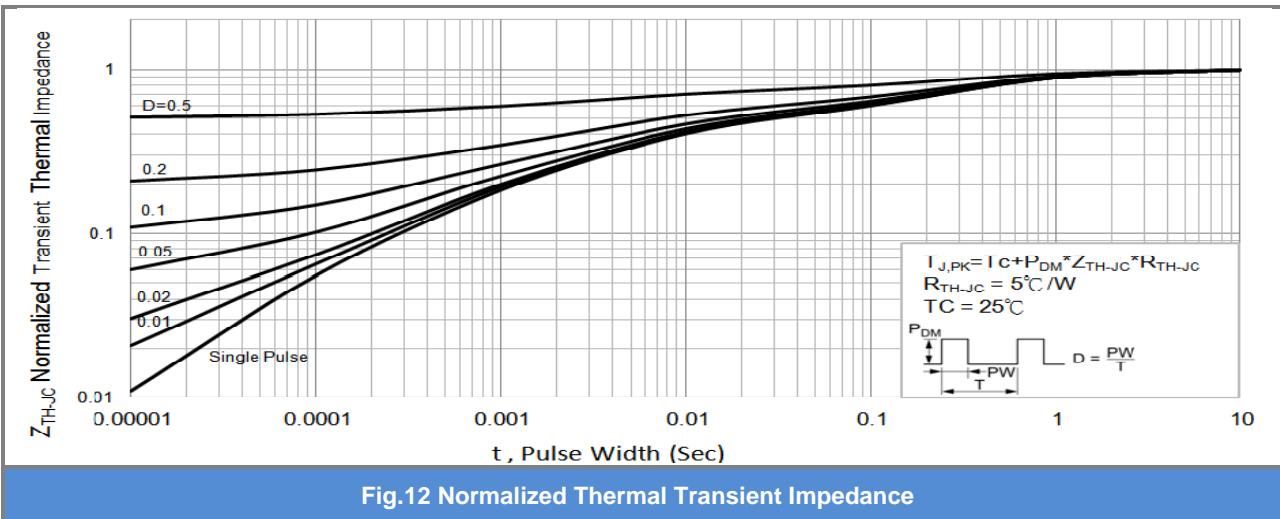
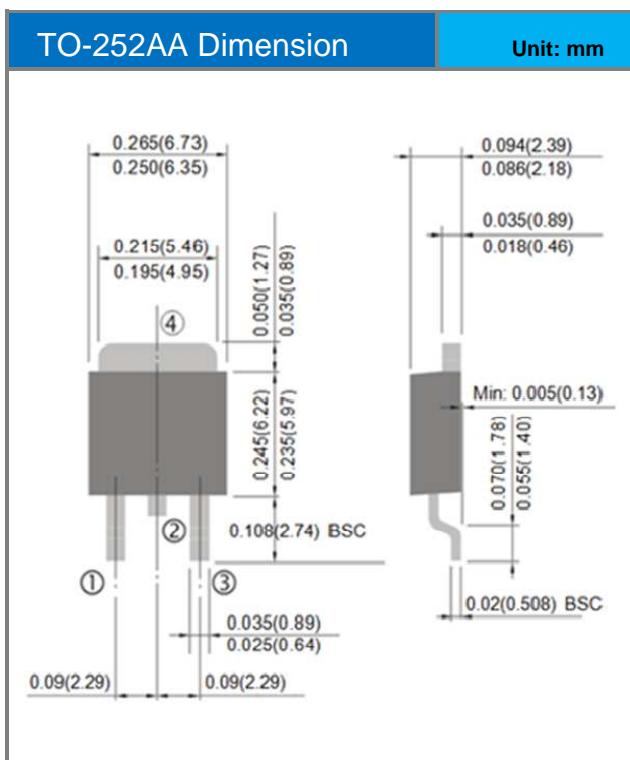


Fig.12 Normalized Thermal Transient Impedance



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Packaging Information





PJD15P06A

PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJD15P06A_L2_00001	TO-252AA	3,000pcs / 13" reel	D15P06A	Halogen free

MOUNTING PAD LAYOUT

